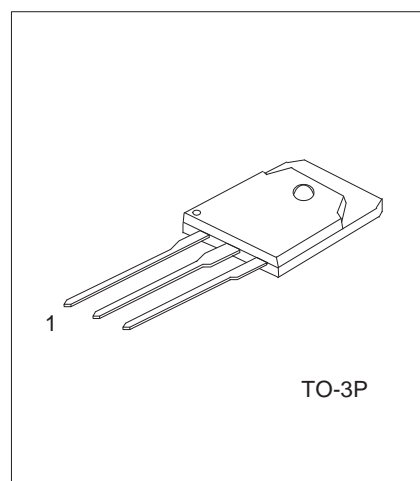


PNP EPITAXIAL SILICON TRANSISTOR

HIGH POWER AMPLIFIER APPLICATION

FEATURES

- * Complementary to 2SD718.
- * Recommended for 45 ~ 50W Audio Frequency Amplifier Output Stage.



1: BASE 2: COLLECTOR 3: EMITTER

*Pb-free plating product number: 2SB688L

ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-10	A
Base Current	I_B	-1	A
Collector Power Dissipation (T _C =25°C)	P_C	80	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-40 ~ +150	°C

ELECTRICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-10	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-120			V
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -1A$	55		160	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -5A, I_B = -0.5A$			-2.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5A, I_C = -5A$			-1.5	V
Transition Frequency	f_T	$V_{CE} = -5A, I_C = -1A$		10		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f=1MHz$		280		pF

CLASSIFICATION OF hFE

RANK	R	O
RANGE	55 ~ 110	80 ~ 160

